

INTEGRATED CIRCUIT HAVING A DOPED POROUS  
DIELECTRIC AND METHOD OF MANUFACTURING THE SAME

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ABSTRACT OF THE DISCLOSURE

In one aspect of the invention, a method for forming an integrated circuit having an at least substantially doped porous dielectric includes forming a semiconductor device. The semiconductor device includes at least a portion of a semiconductor substrate. The method also includes forming a dielectric layer disposed outwardly from the semiconductor substrate and surrounding at least a portion of the semiconductor device. The dielectric layer includes an at least substantially porous dielectric material doped with at least one dopant. In addition, the method includes forming a contact layer disposed outwardly from the dielectric layer and operable to provide electrical connection to the semiconductor device.

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